

IN THE CLAIMS:

1. (Currently Amended) A semiconductor device comprising:
peripheral electrodes formed on a periphery of a
semiconductor chip;

internal electrodes formed inside the peripheral electrodes
on the semiconductor chip; and

circuits formed in the semiconductor chip,

wherein the peripheral electrodes are connected to the
circuits by an internal line, and the internal electrodes are
connected to the circuits and the peripheral electrodes by the
internal line, and

wherein the same signal is either an input and/or output
either to or from both an internal electrode and peripheral
electrode.

2. (Original) A semiconductor device according to Claim 1,
wherein the internal electrodes are smaller than the peripheral
electrodes.

3. (Original) A semiconductor device according to Claim 1,
wherein the internal electrodes comprise at least one selected
from the group consisting of a power supply terminal, a ground
terminal, and a clock terminal.

4. (Currently Amended) A semiconductor device according to Claim 1, wherein the peripheral electrodes not connected to the internal electrodes are used as terminals for RF ~~high-frequency~~ signals.

5. (Original) A semiconductor device comprising:
peripheral electrodes formed on a periphery of a semiconductor chip;
internal electrodes formed inside the peripheral electrodes on the semiconductor chip; and
circuits formed in the semiconductor chip,
wherein the peripheral electrodes are connected to the circuits by an internal line, the internal electrodes are connected to the circuits and the peripheral electrodes by the internal line, and the internal electrodes are also connected to rewired lines, the rewired lines formed above the internal electrodes with an insulating layer therebetween, and at ends of the rewired lines formed area array electrodes.

6. (Original) A semiconductor device comprising:
peripheral electrodes formed on a periphery of a semiconductor chip;

internal electrodes formed inside the peripheral electrodes on the semiconductor chip;

area array electrodes connected to selected one of the peripheral electrodes and the internal electrodes and formed on the semiconductor chip; and

circuits formed in the semiconductor chip,

wherein the peripheral electrodes are connected to the circuits by an internal line, the internal electrodes are connected to the circuits and the peripheral electrodes by the internal line, and the area array electrodes comprise first area array electrodes connected to the internal electrodes by rewired lines and second area array electrodes connected to the peripheral electrodes by rewired lines.

7. (Original) A semiconductor device according to Claim 6, wherein the first area array electrodes comprise at least one selected from the group consisting of a power supply terminal, a ground terminal, and a clock terminal.

8. (Currently Amended) A semiconductor device according to Claim 6, wherein the second area array electrodes are used as terminals for RF ~~high-frequency~~ signals.